

No.2798A

PNP Epitaxial Planar Silicon Transistor

High-Frequency General-Purpose Amp Applications

### **Applications**

· Ideally suited for use in FM RF amplifiers, mixers, oscillators, converters, and IF amplifiers.

#### **Features**

- · High power gain: PG = 22dB typ (f = 100MHz).
- $\cdot$  Very small-sized package permitting 2SA1688-applied sets to be made small and slim.

Absolute Maximum Ratings at Ta = 25°C					unit		
Collector-to-Base Voltage	$V_{CBO}$		-	-30	V		
Collector-to-Emitter Voltage	$V_{CEO}$		-	-20	V		
Emitter-to-Base Voltage	$V_{EBO}$			-5	v		
Collector Current	$I_{\mathbf{C}}$		-	-30	mA		
Collector Dissipation	$\tilde{P_C}$			150	W		
Junction Temperature	Тj			150	$^{\circ}\mathrm{C}$		
Storage Temperature	Tstg		-55  to  +150		$^{\circ}\mathrm{C}$		
Electrical Characteristics at Ta = 25°C			min	typ	max	unit	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -10V, I_E = 0$			-0.1	$\mu \mathbf{A}$	
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -4V, I_{C} = 0$			-0.1	μA	
DC Current Gain	$h_{FE}$	$V_{CE} = -6V$ , $I_{C} = -1mA$	60%	•	270	270※	
Gain-Bandwidth Product	$\mathbf{f_T}$	$V_{CE} = -6V, I_{C} = -1mA$	150	230		MHz	
Reverse Transfer Capacitance	Cre	$V_{CB} = -6V$ , $f = 1MHz$		1.1	1.7	$\mathbf{pF}$	
Base-to-Collector Time Constant	r <sub>bb</sub> 'Cc	$V_{CE} = -6V, I_C = -1mA,$		11	20	$\mathbf{p}\mathbf{s}$	
		f=31.9MHz					
Voltage Gain	PG	See specified Test Circuit.		22		dΒ	
Noise Figure	NF	$V_{CE} = -6V, I_{C} = -1mA,$		2.5		dΒ	
		$\int f = 100 MHz$					

### \* : The 2SA1688 is classified by 1mA her as follows :

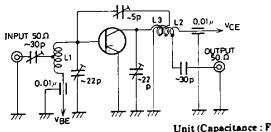
-										
	60	3	120	90	4	180	135	5	270	

Note) Marking: E

 $h_{FE}$  rank: 3, 4, 5

For CP package version, use the 2SA1256.

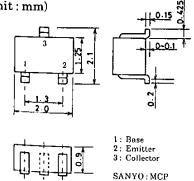
## NF, PG Test Circuit



Unit (Capacitance : F)

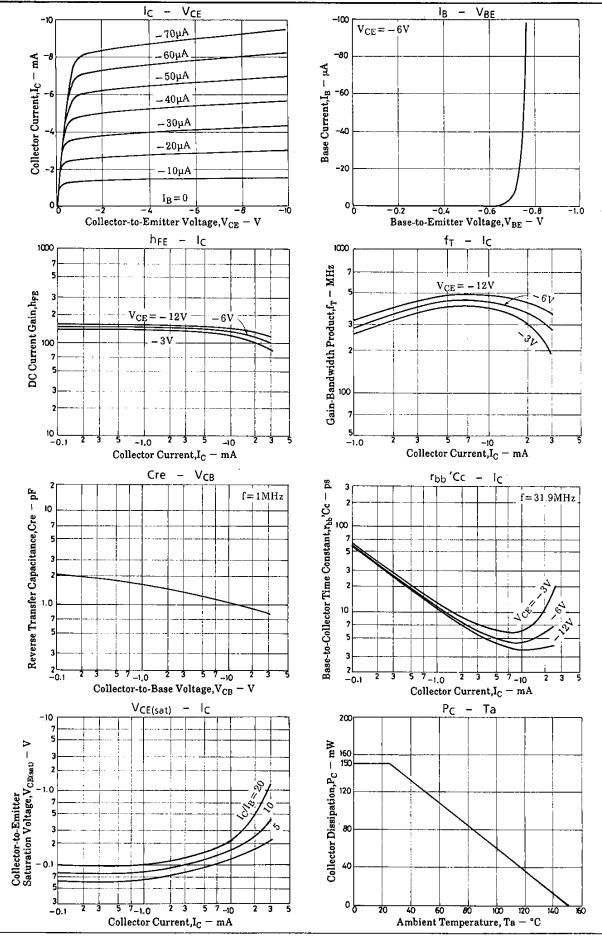
L1: 1 mms plated wire 10 mms 5T, tap: 2T from VBz side L2: 1 mms plated wire 10 mms 7T, tap: 1T from VCz side L3: 1 mms enamel wire 10 mms 3T

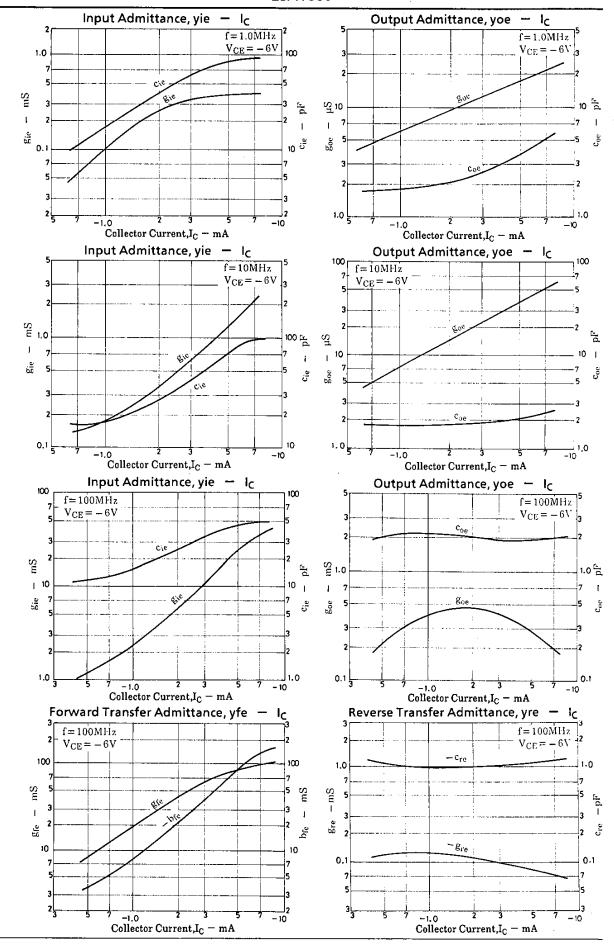
# Package Dimensions 2059A (unit:mm)

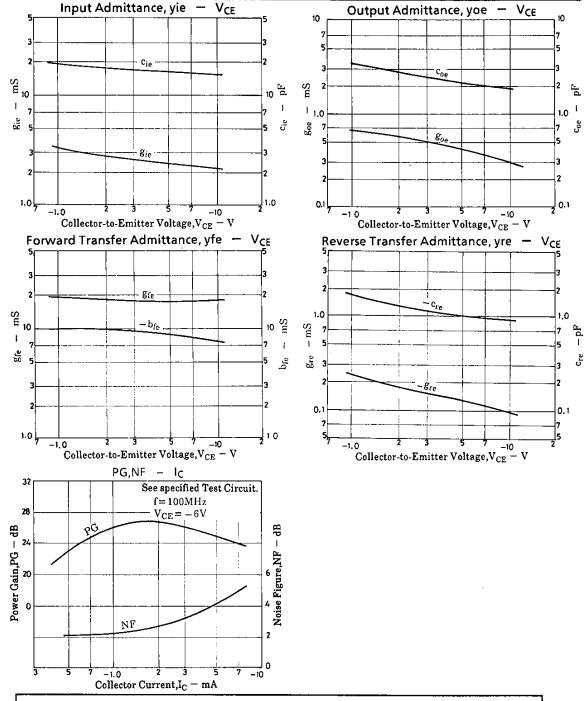


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